

Electronic Supplementary Information (ESI)

Large tunneling magnetoresistance in magnetic tunneling junctions based on two-dimensional CrX_3 ($\text{X}=\text{Br}, \text{I}$) monolayers

Longfei Pan,^a Le Huang,^b Mianzeng Zhong,^a Xiang-Wei Jiang,^a Hui-Xiong Deng,^a Jingbo Li,^a Jian-Bai Xia,^a
and Zhongming Wei^{*a}

a. A State Key Laboratory of Superlattices and Microstructures, Institute of Semiconductors,
Chinese Academy of Sciences & College of Materials Science and Opto-Electronic Technology,
University of Chinese Academy of Sciences, Beijing 100083, China.

b. School of Materials and Energy, Guangdong University of Technology, Guangzhou,
Guangdong 510006, China

Corresponding author: zmwei@semi.ac.cn

Supplementary Figures

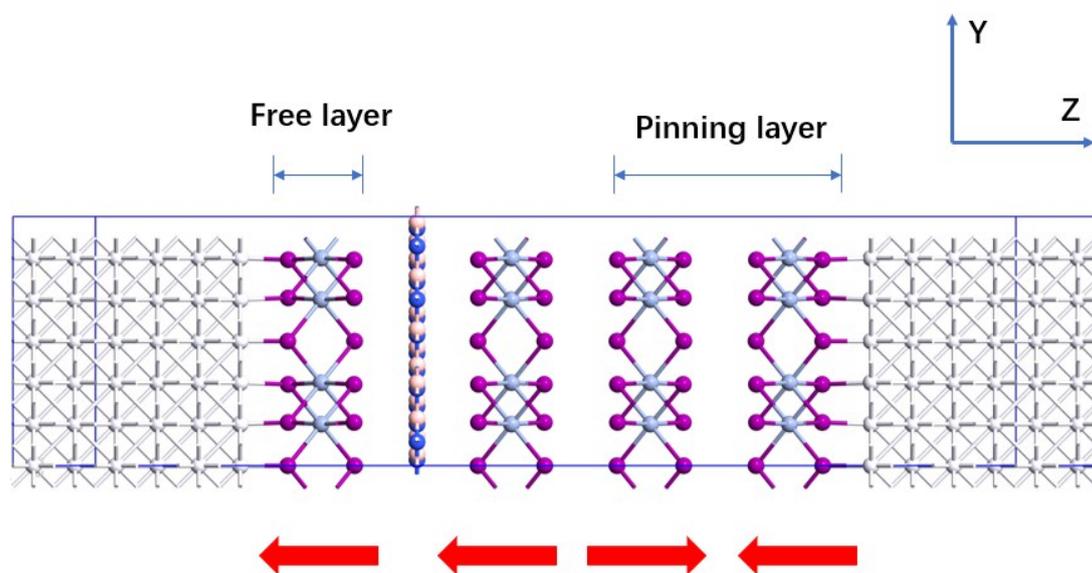


Fig. S1. Schematic of a complete device with a pinning layer. The red arrows represent the possible magnetic moment direction of the CrI_3 layers. The left and right parts are Pt electrodes. h-BN monolayer is sandwiched in CrI_3 layers.

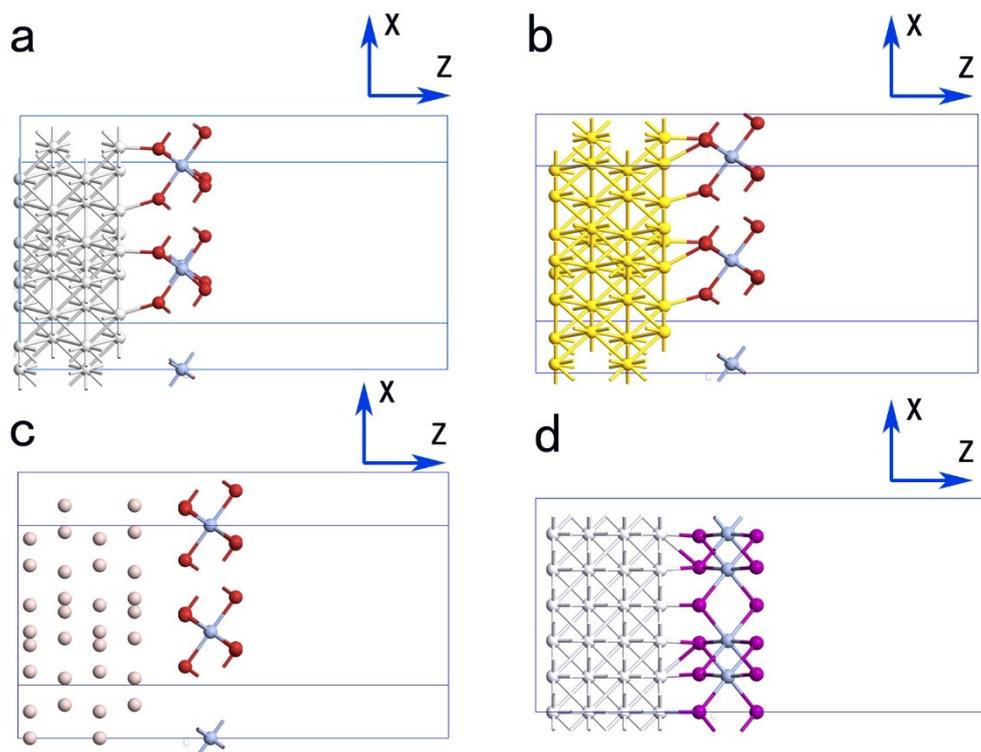


Fig. S2. Schematics of (a) Ag-CrBr₃; (b) Au-CrBr₃; (c) Al-CrBr₃; and (d) Pt-CrI₃ contacts used in our calculations.

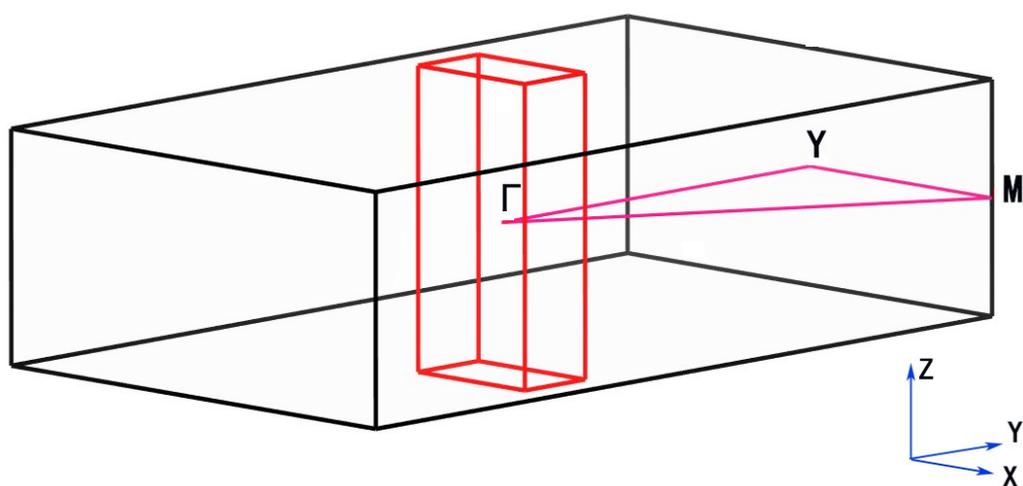


Fig. S3. Schematic of the Brillouin zone of CrI₃-Pt contact. The red frame represents the shape of the true unit cell. The black box represents the Brillouin zone. The symmetry k-points used in the calculation are marked in the figure.